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RFMD(R) Introduces Family of Multi-Use Distributed Amplifiers for Broadband, High-Frequency Applications

New Amplifiers Deliver Superior Gain and Output Power, Up to 35 GHz

GREENSBORO, N.C., June 18, 2009 (GLOBE NEWSWIRE) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance semiconductor components, today announced the addition of five new distributed amplifiers for broadband, high-frequency applications. The new amplifiers deliver superior gain and output power (up to 35 GHz) and are designed to support a wide array of high frequency commercial, military and space applications.

Based upon GaAs pseudomorphic high electron mobility transistor (pHEMT) technology, the SDA-1000 through 5000 series of distributed amplifiers range in operating frequency from DC-20 GHz to DC-35 GHz and represent the first RFMD amplifiers with operation above 20 GHz. Two follow-on high-performance amplifiers, to be introduced as an extension to this product family, will deliver similar wideband high-frequency performance and excellent noise figure and will increase operating frequency up to 50 GHz.

"We are pleased to introduce this new family of distributed amplifiers which have been designed specifically for high-frequency applications such as modulators, broadband test equipment, wideband gain blocks in military and space applications and Mach Zehnder Modulator (MZM) laser drivers and clock drivers in fiber optics. These new products deliver superior performance and provide a solid foundation for our broadband microwave amplifier product family," said Jeff Shealy, general manager of RFMD's Defense and Power business unit.

Additionally, Kevin Kobayashi, RFMD Fellow, stated, "We are also developing products with higher sensitivity, linearity and multi-Watt power output exploiting advanced semiconductors like Gallium Nitride and Indium Phosphide. Recently, we demonstrated as much as 4 times greater linearity and output power for GaN-based distributed amplifiers without compromising bandwidth or noise figure compared to our GaAs pHEMT products. These will be attractive solutions for emerging applications and systems such as software reconfigurable radios and 100 gigabit ethernet."

The GaN MMIC performance was presented by Kobayashi at the Radio Frequency Integrated Circuits symposium during the IEEE MTT-S International Microwave Symposium held June 6 through June 12.

Technical features of the featured SDA products include:

Design		SDA-1000	SDA-2000	SDA-3000	SDA-4000	SDA-5000	SDA-6000	SDA-7000
Operating Frequency	GHz	DC-20	DC-22	DC-24	DC-26	DC-35	DC-50	DC-40
P1dB @ mid band	dBm	25	26	24	20	17	15	22
Gain @ mid band	dB	17	12	17.1	15	12	8.5	12
IP3 @ mid band*	dB	36*	38*	34*	30*	27*	25.0	36.0
NF @ mid band	dB	3.5	5.0	2.1	3.0	3.0	~3.7	~5
Supply Voltage	V	8.0	8.0	8.0	5.0	6.5	5.0	8.0
Supply Current	mA	300.0	400.0	160.0	160.0	80.0	100	200.0

Availability

Samples of the SDA-1000, -2000, -3000, -4000 and -5000 distributed amplifiers are available immediately and product revenue is expected in the September 2009 quarter.

About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance semiconductor components. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the cellular handset, wireless infrastructure, wireless local area network (WLAN), CATV/broadband and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at www.rfmd.com.

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including variability in quarterly operating results, the impact of global macroeconomic and credit conditions on our business, the rate of growth and development of wireless markets, risks associated with our planned exit from our wireless systems business, including cellular transceivers and GPS solutions, the risk that restructuring charges may be greater than originally anticipated and that the cost savings and other benefits from the restructuring may not be achieved, risks associated with the operation of our wafer fabrication facilities, molecular beam epitaxy facility, assembly facility and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, our ability to reduce costs and improve gross margins by implementing innovative technologies, our ability to bring new products to market, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on a limited number of customers, and dependence on third parties. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

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